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IN THE CLAIMS:

E1 34. (Three Times Amended) A semiconductor device, comprising:
a conductor layer formed on a semiconductor substrate;
a dielectric film formed on the conductor layer; and
a conductor line formed on the dielectric film, wherein
the conductor layer is not formed in a region directly below the conductor line but in both
sides of the region thereof, and
the dielectric film consists of two dielectric layers with mutually different dielectric
constants.
